

N-Channel JFET

15 V, 10 to 32 mA, 35 mS, CP

2SK3557

Applications

- AM Tuner RF Amplification
- Low Noise Amplifier

Features

- Large | yfs |
- Small Ciss
- Ultrasmall-sized Package Permitting 2SK3557-applied Sets to be Made Smaller and Slimer
- Ultralow Noise Figure
- These are Pb-Free Devices

Product & Package Information

• Package: CP

• JEITA, JEDEC: SC-59, TO-236, SOT-23, TO-236AB

• Minimum Packing Quantity: 3,000 Pcs./Reel

Specifications

ABSOLUTE MAXIMUM RATINGS (at Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSX}		15	V
Gate-to-Drain Voltage	V_{GDS}		-15	V
Gate Current	I _G		10	mA
Drain Current	I _D		50	mA
Allowable Power Dissipation	P _D		200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

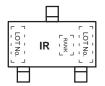
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



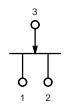
- 1: Source
- 2: Drain
- 3: Gate

SC-59 / CP3 CASE 318BJ

MARKING DIAGRAM



ELECTRICAL CONNECTION



ORDERING INFORMATION

Device	Package	Shipping [†]
2SK3557-6-TD-E	CP (Pb-Free)	3,000 / Tape & Reel
2SK3557-7-TD-E	CP (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (at Ta = 25°C)

			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Gate-to-Drain Breakdown Voltage	V _{(BR)GDS}	$I_G = -10 \mu A, V_{DS} = 0 V$	-15	-	_	V
Gate Cutoff Current	I _{GSS}	$V_{G S} = -10 V, V_{DS} = 0 V$	-	-	-1.0	nA
Cutoff Voltage	V _{GS} (off)	$V_{DS} = 5 \text{ V}, I_{D} = 100 \mu\text{A}$	-0.3	-0.7	-1.5	V
Drain Current	I _{DSS}	V _{DS} = 5 V, V _{GS} = 0 V	10*	-	32*	mA
Forward Transfer Admittance	yfs	$V_{DS} = 5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ kHz}$	24	35	_	mS
Input Capacitance	Ciss	V _{DS} = 5 V, V _{GS} = 0 V, f = 1 MHz	_	10.0	_	pF
Reverse Transfer Capacitance	Crss	V _{DS} = 5 V, V _{GS} = 0 V, f = 1 MHz	-	2.9	-	pF
Noise Figure	NF	$V_{DS} = 5 \text{ V}, R_g = 1 \text{ k}\Omega, I_D = 1 \text{ mA},$ f = 1 kHz	-	1.0	_	dB

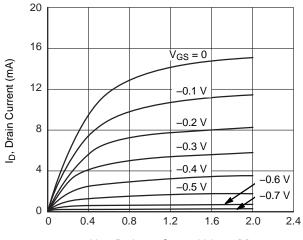
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*The 2SK3557 is classified by I_{DSS} as follows: (unit: mA)

Table 1.

Rank	6	7	
I _{DSS}	10.0 to 20.0	16.0 to 32.0	

2SK3557



V_{DS}, Drain-to-Source Voltage (V)

Figure 1. I_D - V_{DS}

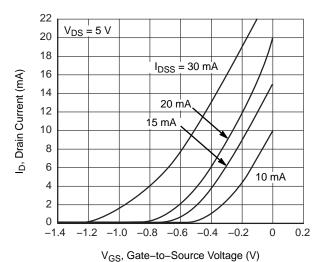


Figure 3. I_D - V_{GS}

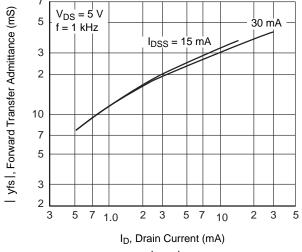
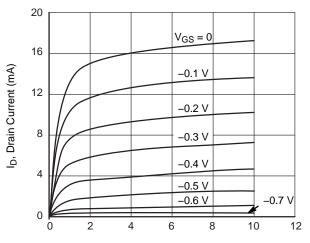


Figure 5. | yfs | - I_D



V_{DS}, Drain-to-Source Voltage (V)

Figure 2. I_D - V_{DS}

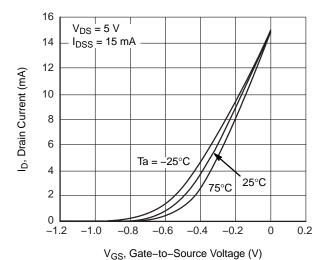


Figure 4. I_D - V_{GS}

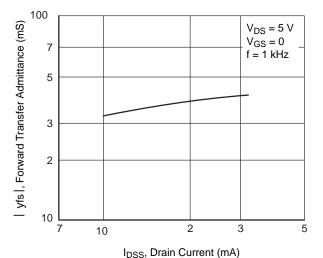


Figure 6. | yfs | - I_D

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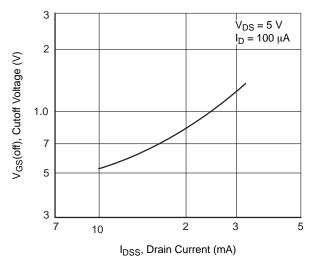


Figure 7. $V_{GS}(off) - I_{DSS}$

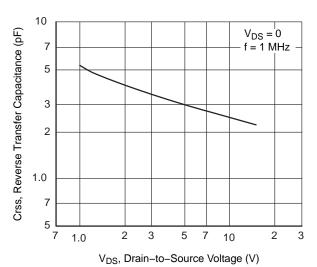


Figure 9. Crss - V_{DS}

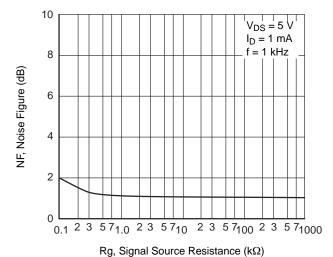


Figure 11. NF - Rg

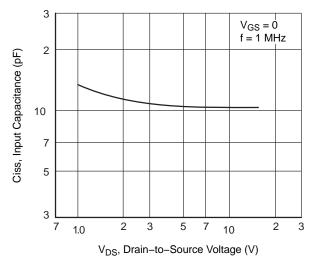


Figure 8. Ciss - V_{DS}

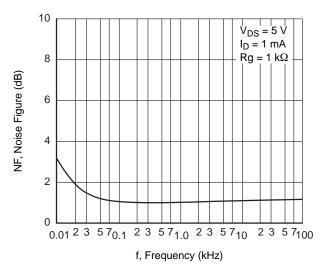


Figure 10. NF - f

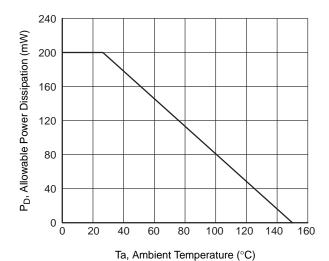


Figure 12. P_D – Ta

Land Pattern Example

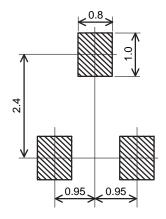


Figure 13. Land Pattern Example

MECHANICAL CASE OUTLINE

3X L

зх b

⊕ 0.10 M C A

C SEATING PLANE

Α

E1

е





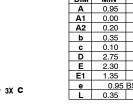
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DATE 09 JAN 2015

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER SIDE.
 4. DIMENSIONS D AND E1 ARE MEASURED AT THE OUTERMOST
- EXTREME OF THE PLASTIC BODY.
 DIMENSIONS 6 AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.10 AND 0.20 FROM THE TIP.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.95	1.35	
A1	0.00	0.10	
A2	0.20 0.40		
b	0.35	0.50	
С	0.10	0.20	
D	2.75	3.05	
E	2.30	2.70	
E1	1.35	1.65	
е	0.95 BSC		
_	0.35	0.75	



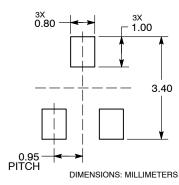
END VIEW

RECOMMENDED **SOLDERING FOOTPRINT***

SIDE VIEW

Δ1

TOP VIEW



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM



XXX = Specific Device Code

Μ = Date Code

= Pb-Free Package

(Note: Microdot may be in either location) *This information is generic. Please refer to

device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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